**PNP/NPN Epitaxial Planar Silicon Transistors** 



2SB1136/2SD1669

# **50V/12A Switching Applications**

## **Applications**

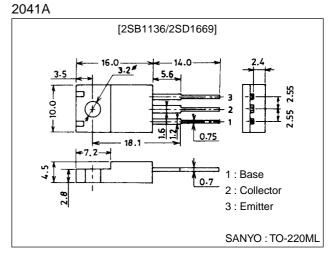
• Relay drivers, high-speed inverters, converters, and other genral high-current switching applications.

## **Features**

- $\cdot$  Low-saturation collector-to-emitter voltage :
- V<sub>CE(sat)</sub>=-0.5V (PNP), 0.4V (NPN) max.
- $\cdot$  Wide ASO leading to high resistance to breakdown.
- · Micaless package facilitating mounting.

## **Package Dimensions**

unit:mm



():2SB1136

## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(–)60	V
Collector-to-Emitter Voltage	VCEO		(–)50	V
Emitter-to-Base Voltage	VEBO		(–)6	V
Collector Current	IC		()12	A
Collector Current (Pulse)	ICP		()15	A
Collector Dissipation	PC		2	W
		Tc=25°C	30	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(–)0.1	mA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(–)0.1	mA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1A	70*		280*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)5A	30			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)1A		10		MHz
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)6A, I <sub>B</sub> =(-)0.6A			(-)0.4	V

 $\ast$  : The 2SB1136/2SD1669 are classified by 1A  $h_{FE}$  as follows :

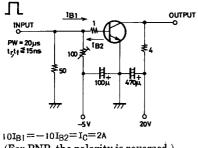
70 Q 140 100 R 200 140 S 280

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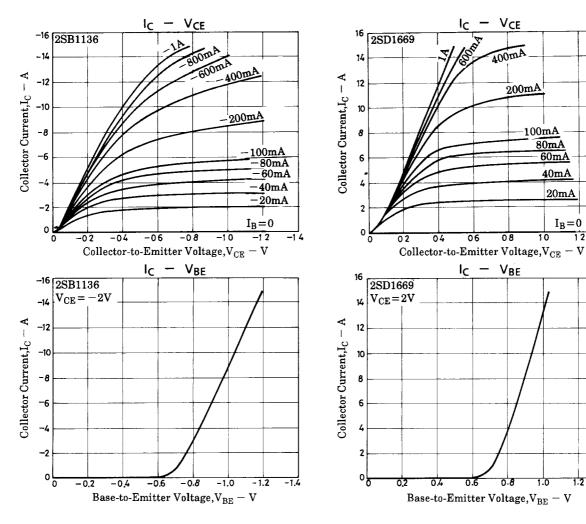
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Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)1mA, I <sub>E</sub> =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> =(−)1mA, R <sub>BE</sub> =∞	(–)50			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =(–)1mA, I <sub>C</sub> =0	(–)6			V
Rise Time	ton	See specified Test Circuti.		(0.2)		μs
				0.1		μs
Storage Time	t <sub>stg</sub>	See specified Test Circuit.		(0.4)		μs
				1.2		μs
Fall Time	t <sub>f</sub>	See specified Test Circuit.		(0.1)		μs
				0.05		μs

### **Switching Time Test Circuit**



(For PNP, the polarity is reversed.) Unit (resistance :  $\Omega$ , capacitance : F)



14

1.2

80mA

60mA

40mA

10

1.0

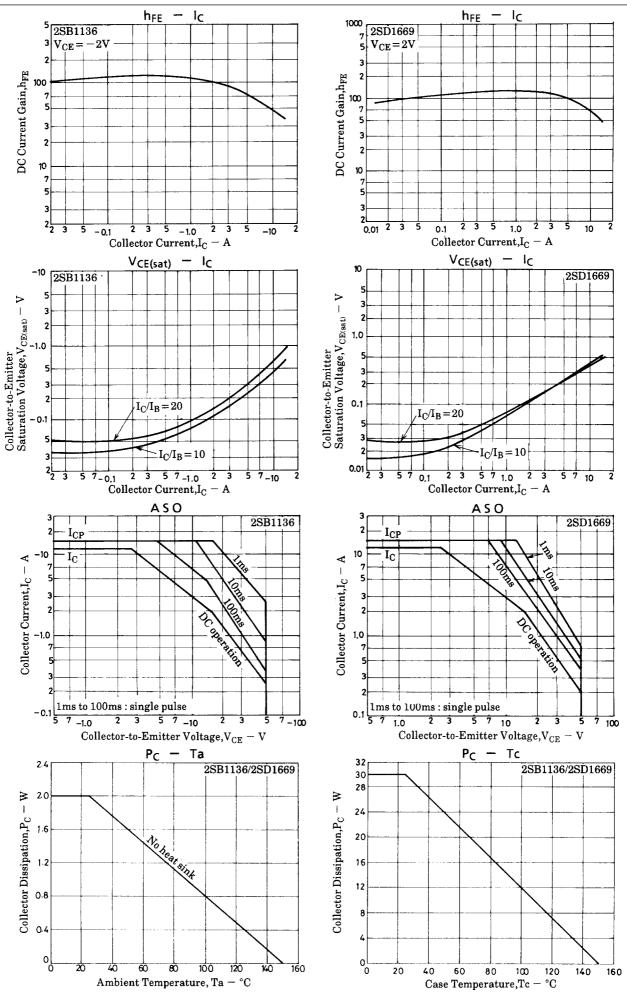
20mA

 $I_B = 0$ 

12

14

### 2SB1136/2SD1669



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